

October 2014

# **KSP44 / KSP45 NPN Epitaxial Silicon Transistor**

### **Features**

- High-Voltage Transistor
- Collector-Emitter Voltage: V<sub>CEO</sub> = KSP44: 400 V KSP45: 350 V



## **Ordering Information**

Part Number	Top Mark	Package	Packing Method	
KSP44BU	KSP44	P44 TO-92 3L Bulk		
KSP44TA	KSP44	TO-92 3L	92 3L Ammo	
KSP44TF	KSP44	TO-92 3L	Tape and Reel	
KSP45TA	KSP45	TO-92 3L	Ammo	

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter		Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	KSP44	500	V	
		KSP45	400		
V <sub>CEO</sub>	Collector-Emitter Voltage	KSP44	400	V	
		KSP45	350		
V <sub>EBO</sub>	Emitter-Base Voltage	6	V		
I <sub>C</sub>	Collector Current	300	mA		
T <sub>J</sub>	Junction Temperature	150	°C		
T <sub>STG</sub>	Storage Temperature	-55 to 150	°C		

### Thermal Characteristics(1)

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit	
В	Power Dissipation	T <sub>A</sub> = 25°C	625	mW
$P_{D}$	Fower Dissipation	T <sub>C</sub> = 25°C	1.5	W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	°C/W	

#### Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

### **Electrical Characteristics**

Values are at  $T_A$  = 25°C unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Max.	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	KSP44	I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0	500		V
		KSP45		400		
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage <sup>(2)</sup>	KSP44	I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0	400		V
PACEO		KSP45		350		
BV <sub>EBO</sub>	Emitter-Base Breakdown Volt	age	$I_E = 100 \mu A, I_C = 0$	6		V
lana	Collector Cut-Off Current KSF		V <sub>CB</sub> = 400 V, I <sub>E</sub> = 0		0.1	
I <sub>CBO</sub>	Collector Cut-Oil Current	KSP45	V <sub>CB</sub> = 320 V, I <sub>E</sub> = 0		0.1	μΑ
1	Collector Cut-Off Current	KSP44	V <sub>CE</sub> = 400 V, I <sub>B</sub> = 0		0.5	
I <sub>CES</sub>		KSP45	V <sub>CE</sub> = 320 V, I <sub>B</sub> = 0		0.5	μΑ
I <sub>EBO</sub>	Emitter Cut-Off Current		$V_{EB} = 4 \text{ V}, I_{C} = 0$		0.1	μΑ
	DC Current Gain <sup>(2)</sup>		$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	40		
h <sub>FE</sub>			$V_{CE}$ = 10 V, $I_{C}$ = 10 mA	50	200	
			$V_{CE}$ = 10 V, $I_{C}$ = 50 mA	45		1
			V <sub>CE</sub> = 10 V, I <sub>C</sub> = 100 mA	40		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage <sup>(2)</sup>		I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0.1 mA	//	0.40	/
			I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA	1	0.50	V
			I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5 mA		0.75	
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage <sup>(2)</sup>		I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA		0.75	V
C <sub>ob</sub>	Output Capacitance		V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0, f = 1 MHz		7	pF

#### Note:

2. Pulse test: pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2\%.$ 

## **Typical Performance Characteristics** V<sub>CE</sub>=10V V<sub>∞</sub>=150V I<sub>∞</sub>/I<sub>g</sub>=10 T<sub>g</sub>=25 °C V<sub>BE</sub>(off)=4V 140 120 DC CURRENT GAIN f[us], TIME 60 40 -20 100 100 I<sub>C</sub>[mA], COLLECTOR CURRENT I<sub>C</sub>[mA], COLLECTOR CURRENT Figure 1. DC Current Gain Figure 2. Turn-On Switching Times T<sub>a</sub>=25 ℃ V<sub>CC</sub>=150V I<sub>C</sub>/I<sub>B</sub>=10 C<sub>ib</sub>[pF], C<sub>ob</sub>[pF], CAPACITANCE T<sub>a</sub>=25 ℃ 100 Cib ([us], TIME 10 Ic[mA], COLLECTOR CURRENT $V_{CB}[V]$ , COLLECTOR-BASE VOLTAGE Figure 3. Turn-Off Switching Times Figure 4. Capacitance T<sub>a</sub>=25 ℃ T<sub>a</sub>=25 ℃ VoE[V] COLLECTOR EMITTER VOLTAGE I<sub>c</sub>=10mA I<sub>c</sub>=50mA $V_{BE}(sat) @I_C/I_B=10$ [V], VOLTAGE 0.3 V<sub>BE</sub>(on) @V<sub>CE</sub>=10V 0.2 V<sub>CE</sub>(sat)@I<sub>C</sub>/I<sub>B</sub>=10 0.0 L 10 0.0 L 0.1 I<sub>c</sub>[mA], COLLECTOR CURRENT $I_{\text{C}}[\text{mA}]$ , COLLECTOR CURRENT Figure 5. On Voltage Figure 6. Collector Saturation Region

# **Typical Performance Characteristics** (Continued)

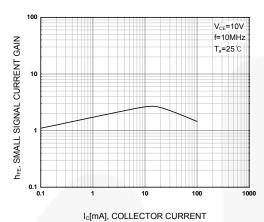


Figure 7. High-Frequency Current Gain

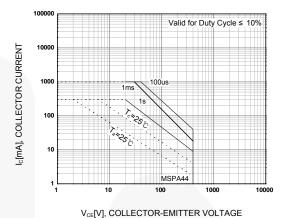
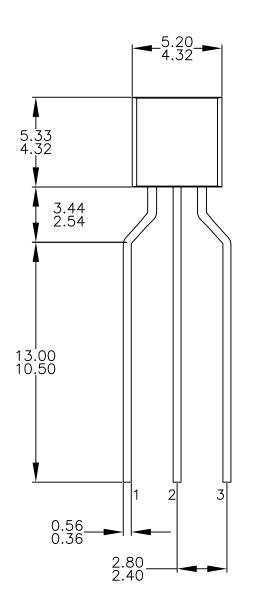
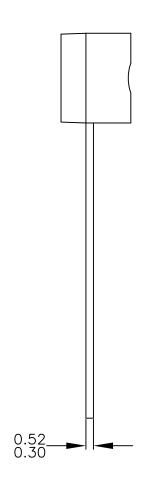
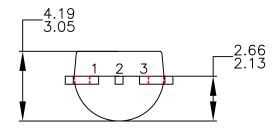


Figure 8. Safe Operating Area

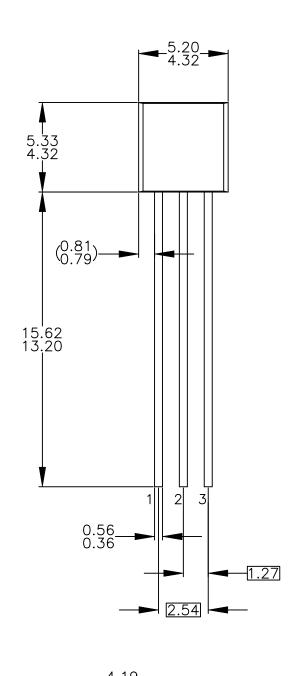


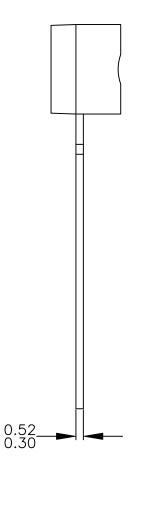




### NOTES: UNLESS OTHERWISE SPECIFIED

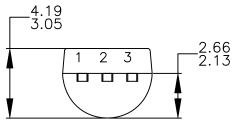
- DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
  ALL DIMENSIONS ARE IN MILLIMETERS.
  DRAWING CONFORMS TO ASME Y14.5M-2009.
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  DRAWING FILENAME: MKT-ZAO3DREV4.









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